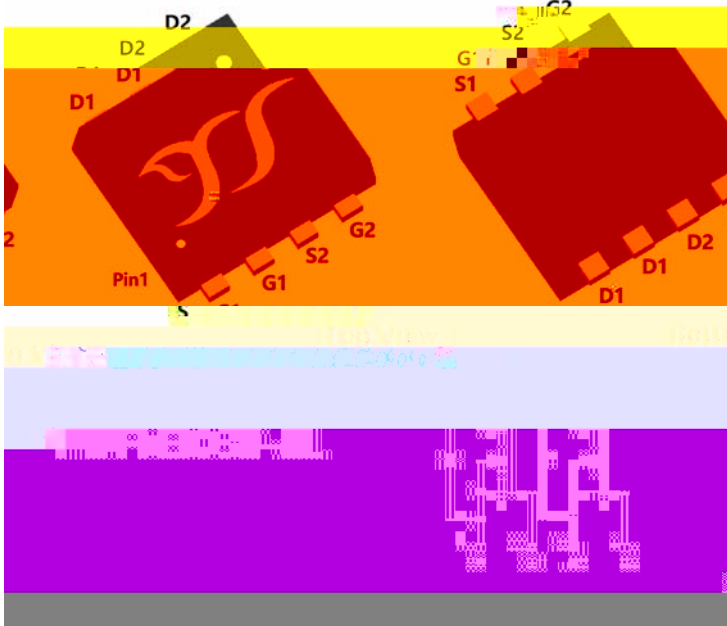


N-Channel and P-Channel Complementary MOSFET


Product Summary
NMOS

V_{DS}	30V
I_D	8A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	19m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	23m

PMOS

V_{DS}	-30V
I_D	-5A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	39m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	54m

General Description

Trench Power LV MOSFET technology
 Excellent package for heat dissipation

I_{HQ}	\hat{A}	'k	h	A	1
-	6	=	A	\hat{A}	

					Unit
Drain-source Voltage		V_{DS}	30	-30	V
Gate-source Voltage		V_{GS}	± 20	± 20	V
Drain Current	$T_A=25$	I_D	8	-5	A
	$T_A=100$		5	-8150	

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Thermal resistance

Parameter	Symbol	NMOS		PMOS		Units	
		Typ	Max	Typ	Max		
Thermal Resistance Junction-to-Ambient ^C	Steady-State	R_{JA}	80	-	90	-	/W

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUL	...
YJU08NP03AJ	F1	Q08NP03A	3000	30000	120000	7" reel



YJU08NP03AJ

PMOS Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$ $V_{DS}=-30V, V$	-	-	-1	μA



NMOS Typical Electrical and Thermal Characteristics Diagrams

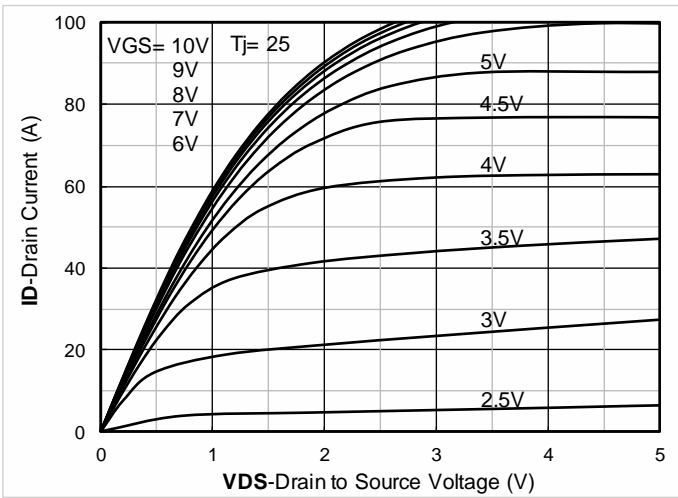


Figure 1. Output Characteristics

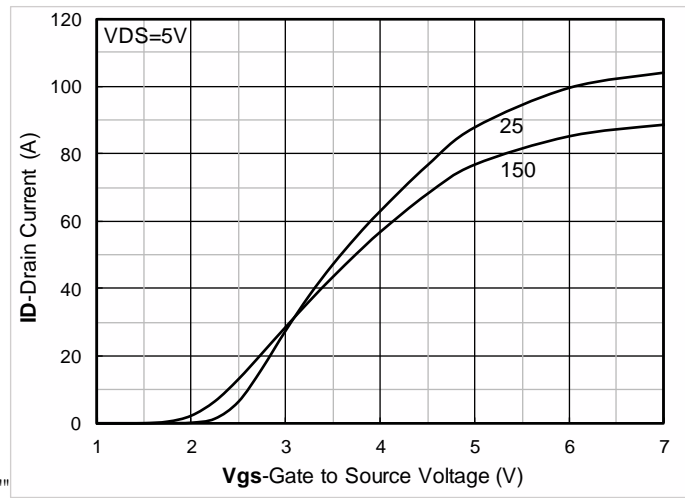


Figure 2. Transfer Characteristics

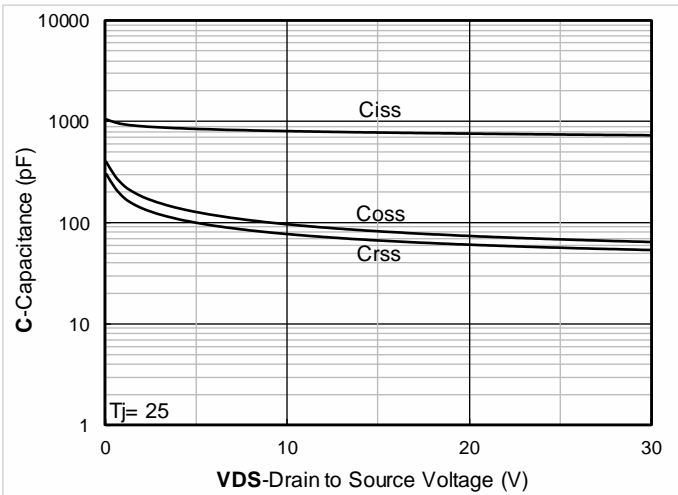


Figure 3. Capacitance Characteristics

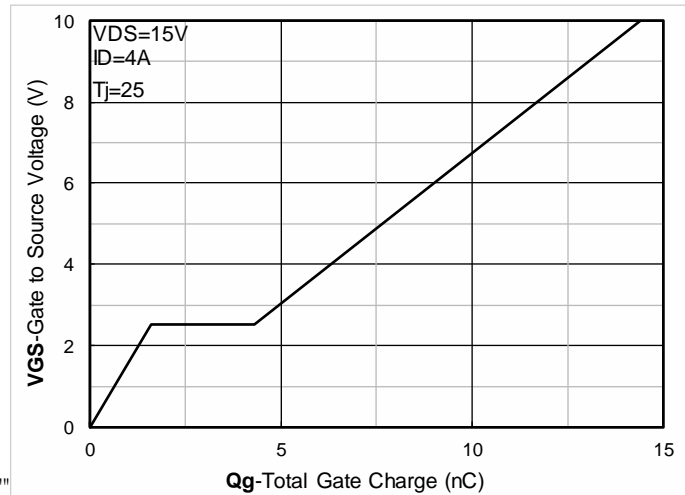


Figure 4. Gate Charge

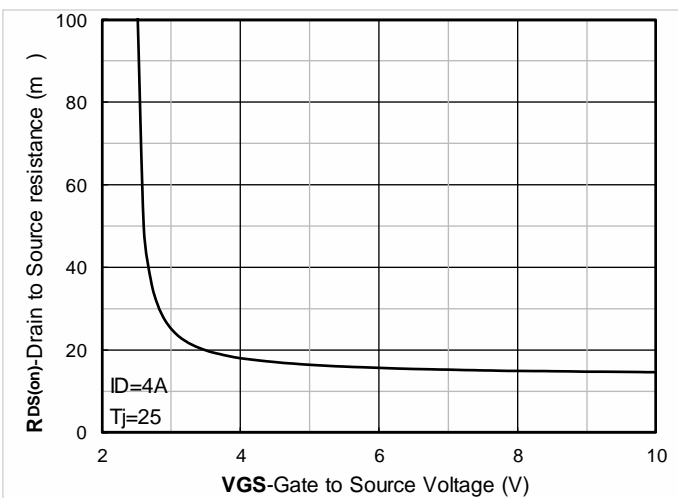


Figure 5. On-Resistance vs Gate to Source Voltage

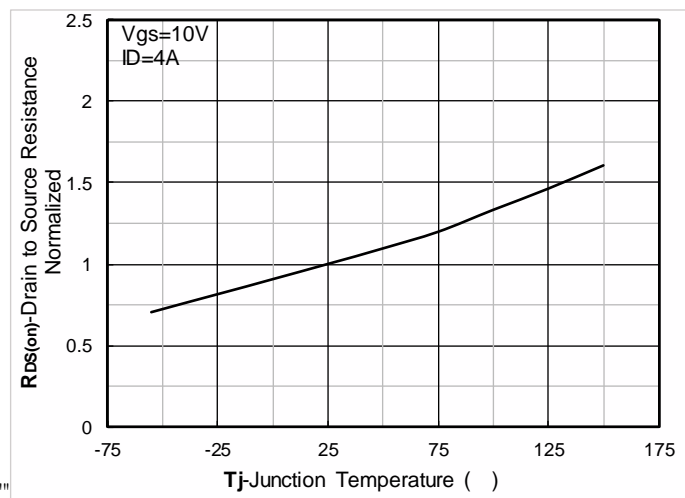


Figure 6. Normalized On-Resistance

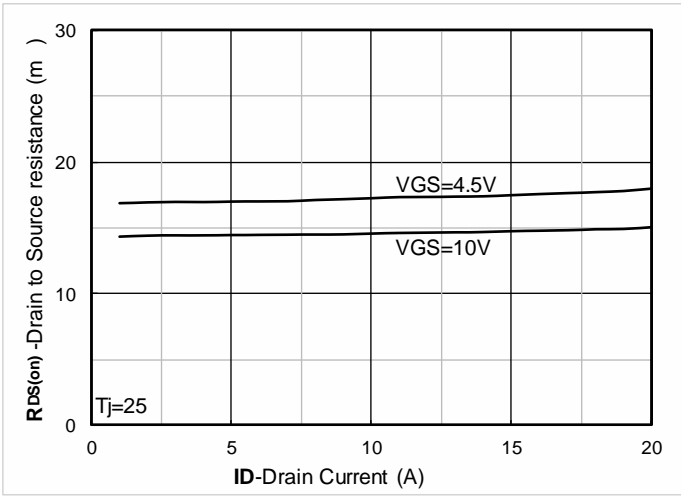


Figure 7. RDS(on) VS Drain Current

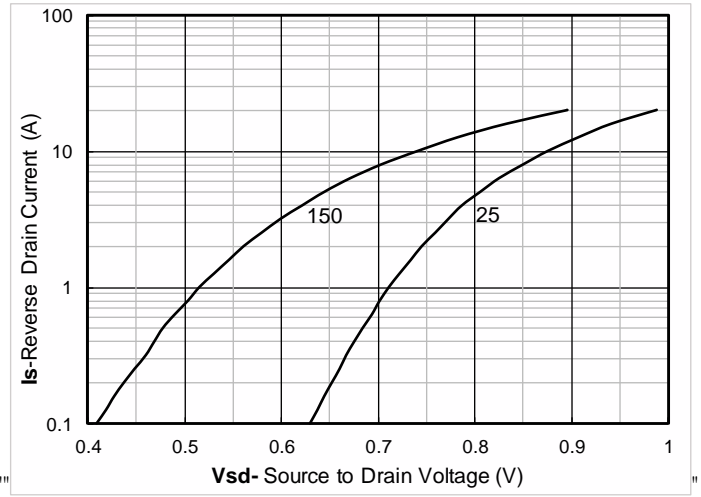
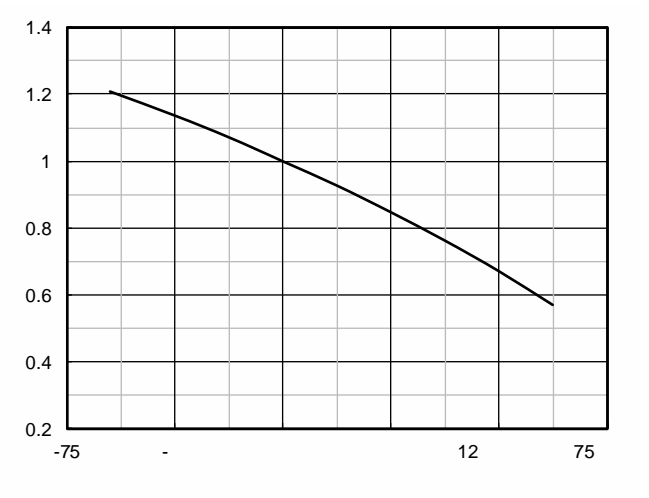
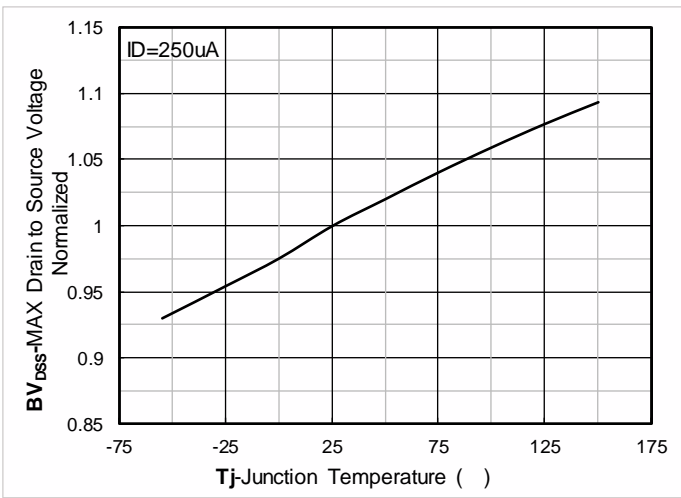
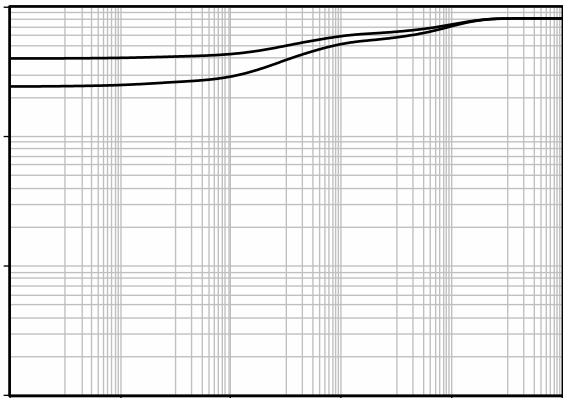


Figure 8. Forward characteristics of reverse diode





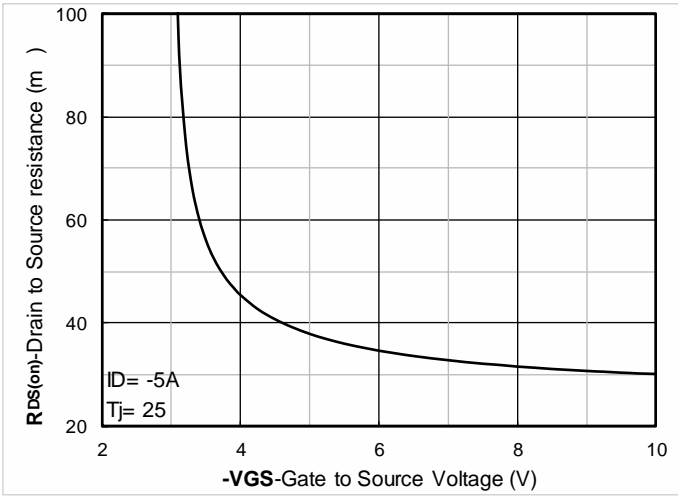


Figure 5. On-Resistance vs Gate to Source Voltage

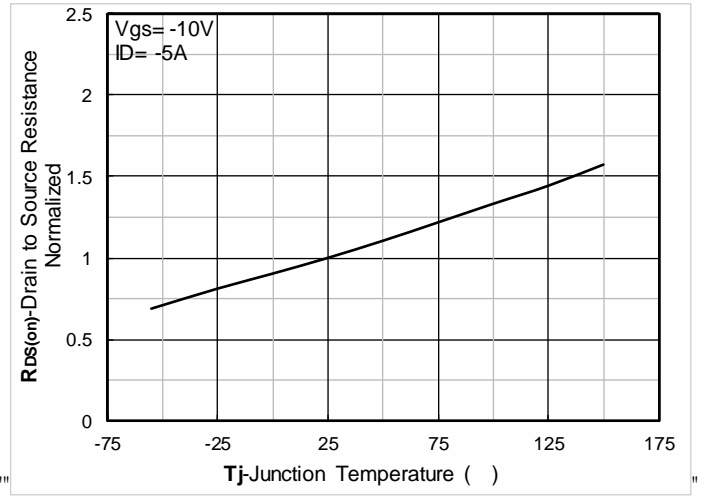


Figure 6. Normalized On-Resistance

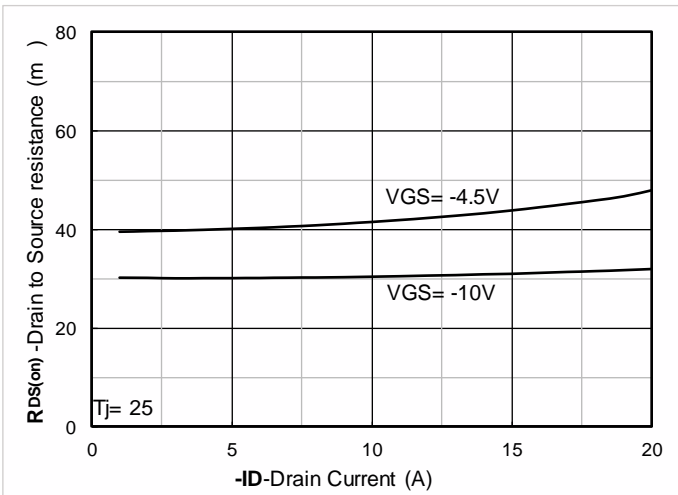


Figure 7. RDS(on) VS Drain Current

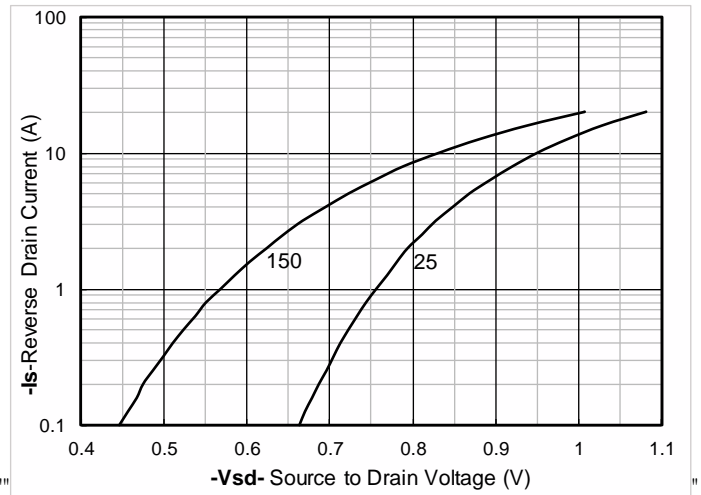
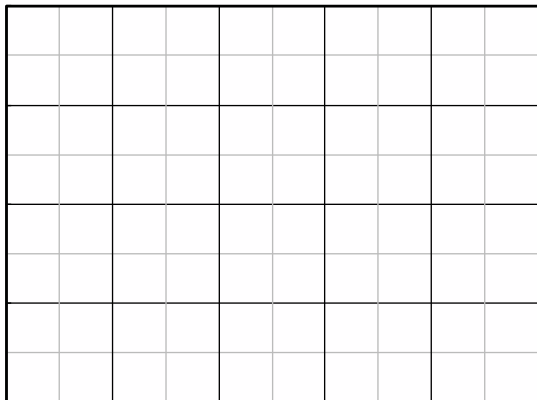
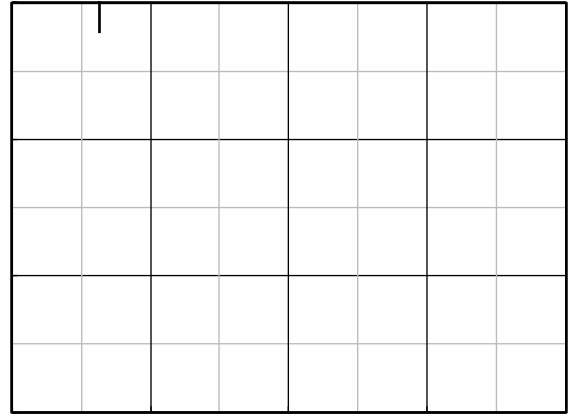
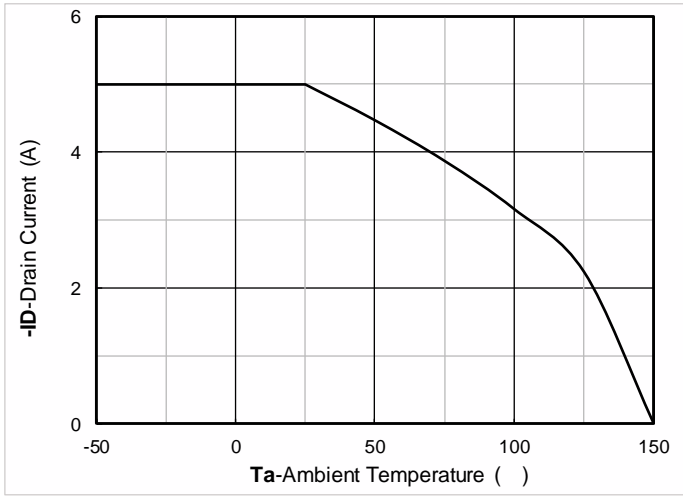


Figure 8. Forward characteristics of reverse diode







PDFN3030-8L Package information

DIMENSIONS

SYMBOL	INCHES		Millimeter
	MIN.	MAX	

TOP VIEW

SIDE VIEW

BOTTOM VIEW

UNIT mm

SUGGESTED SOLDER PAD LAYOUT

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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